

FIG. 1



FIG. 2A

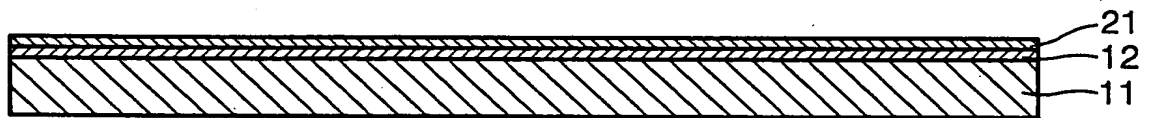


FIG. 2B

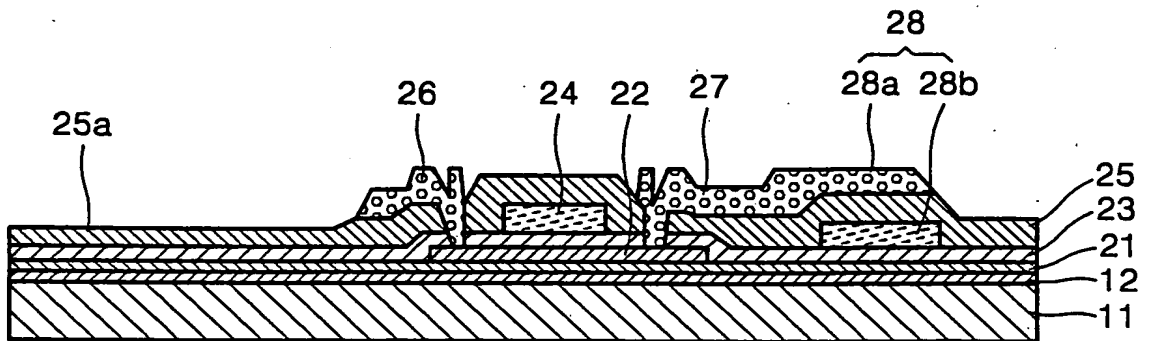


FIG. 2C

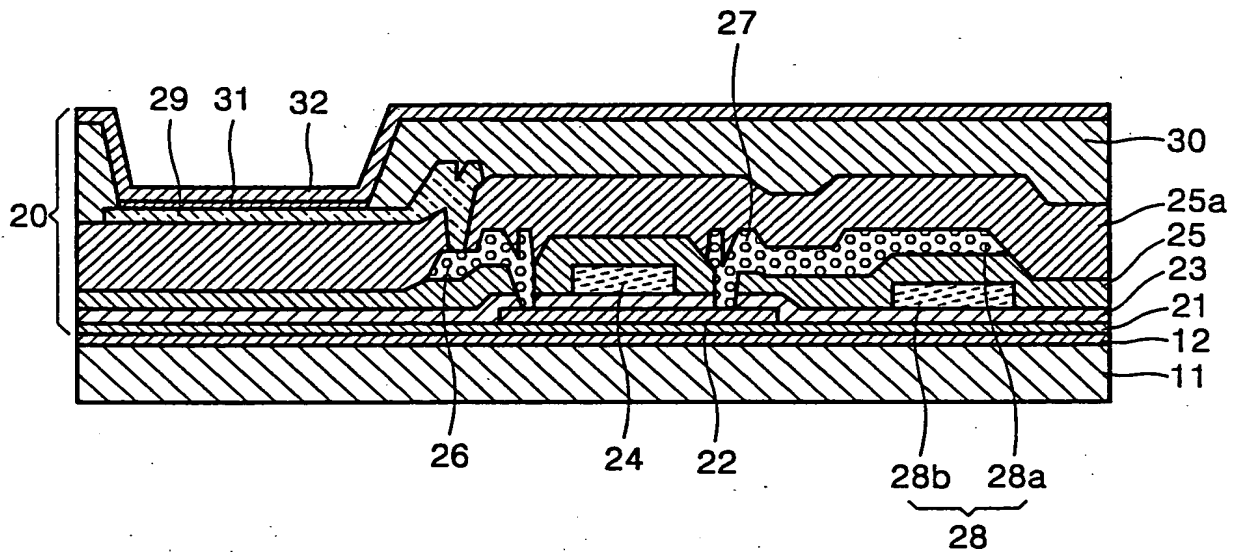


FIG. 3

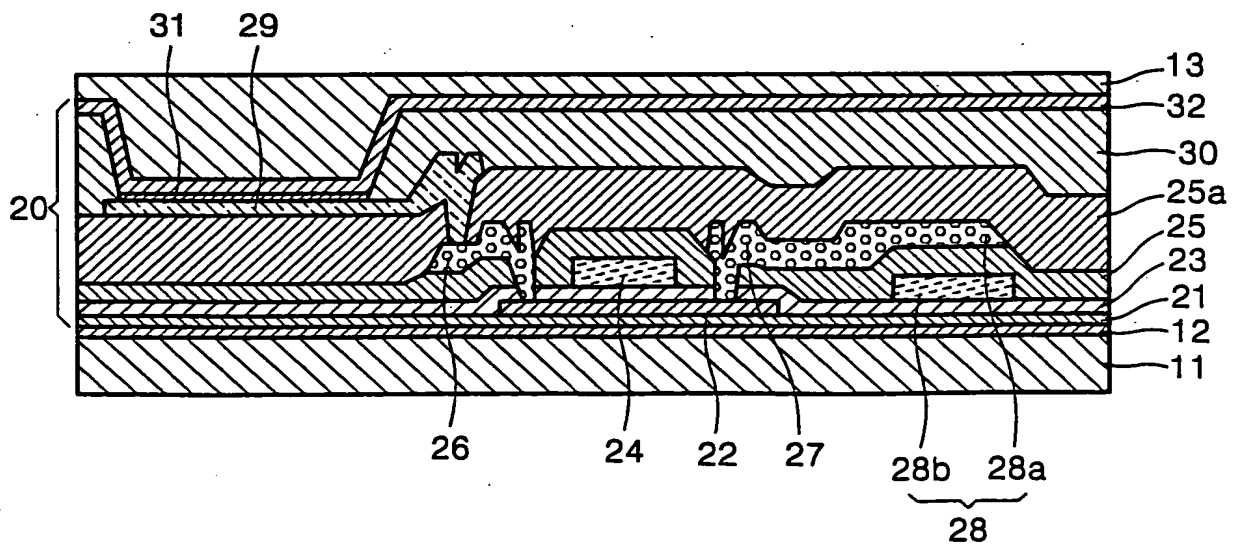


FIG. 4

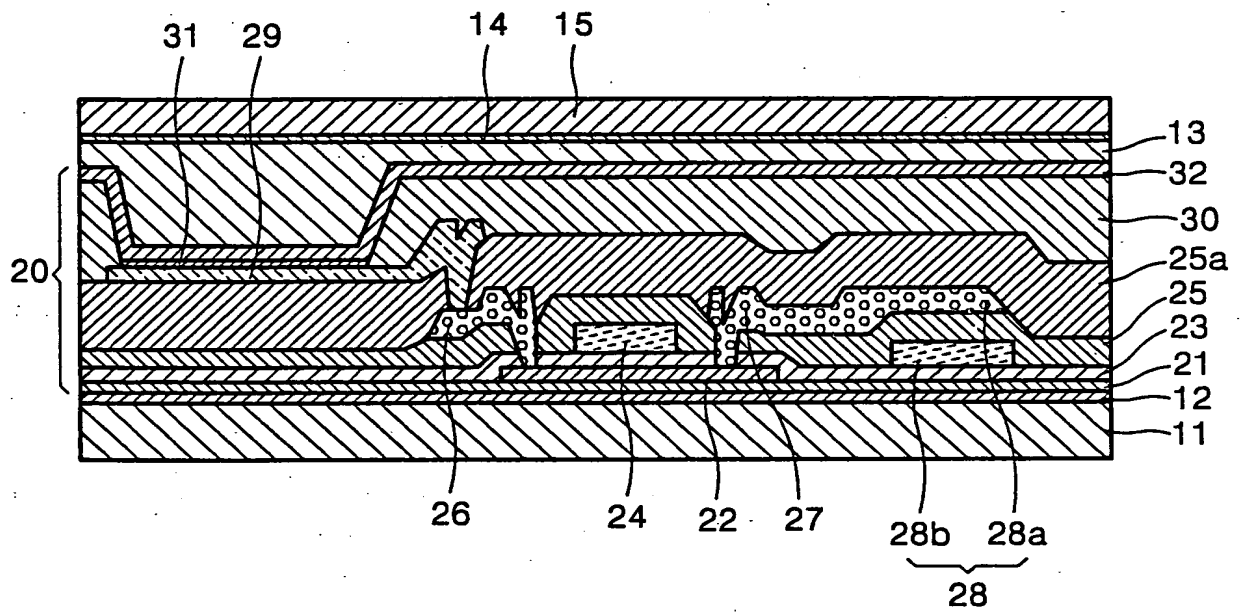
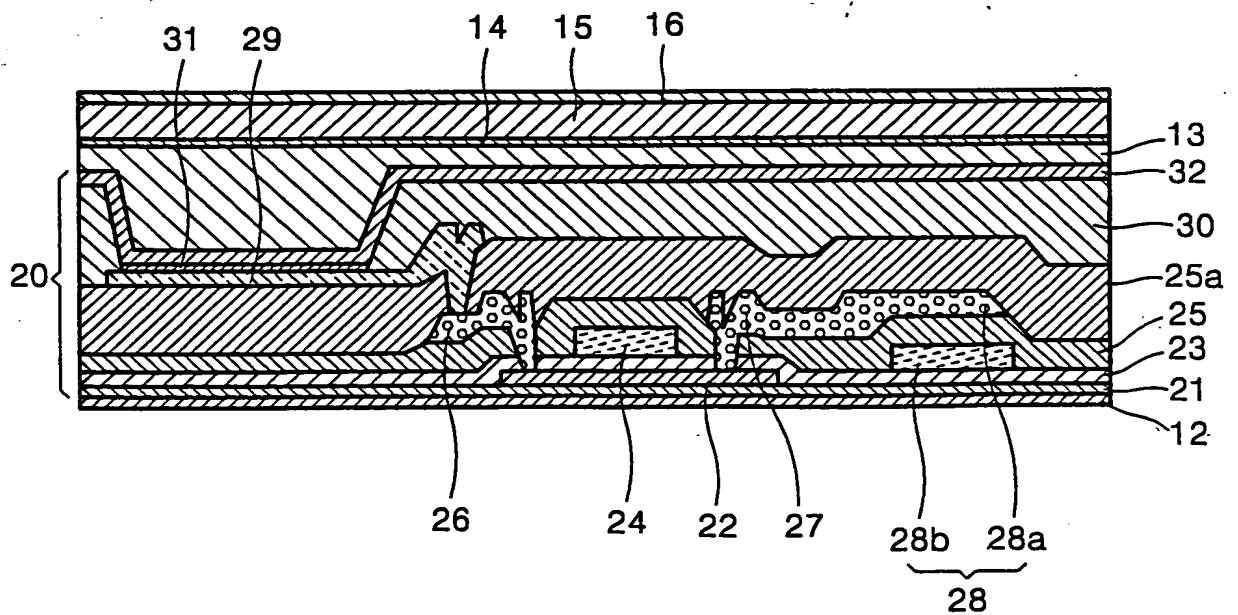


FIG. 5



A detailed cross-sectional view of a semiconductor device. The device consists of a substrate with multiple layers. From top to bottom, the layers are labeled 13, 32, 30, 25a, 25, 23, 21, 12, 11', and 19. A central structure is formed within the substrate, featuring a central core (24) surrounded by a layer (22). This core is flanked by two regions (26 and 27) and is connected to a base layer (28) which is divided into two parts (28a and 28b). The central structure is surrounded by a layer (23) and a layer (25). The top surface of the device is covered by a layer (14) and a layer (15). A layer (16) is also shown. A bracket (20) indicates a specific region on the left side of the device. Other labels include 31, 29, 14, 15, 16, 13, 32, 30, 25a, 25, 23, 21, 12, 11', 19, 26, 24, 22, 27, 28b, 28a, and 28.

FIG. 8

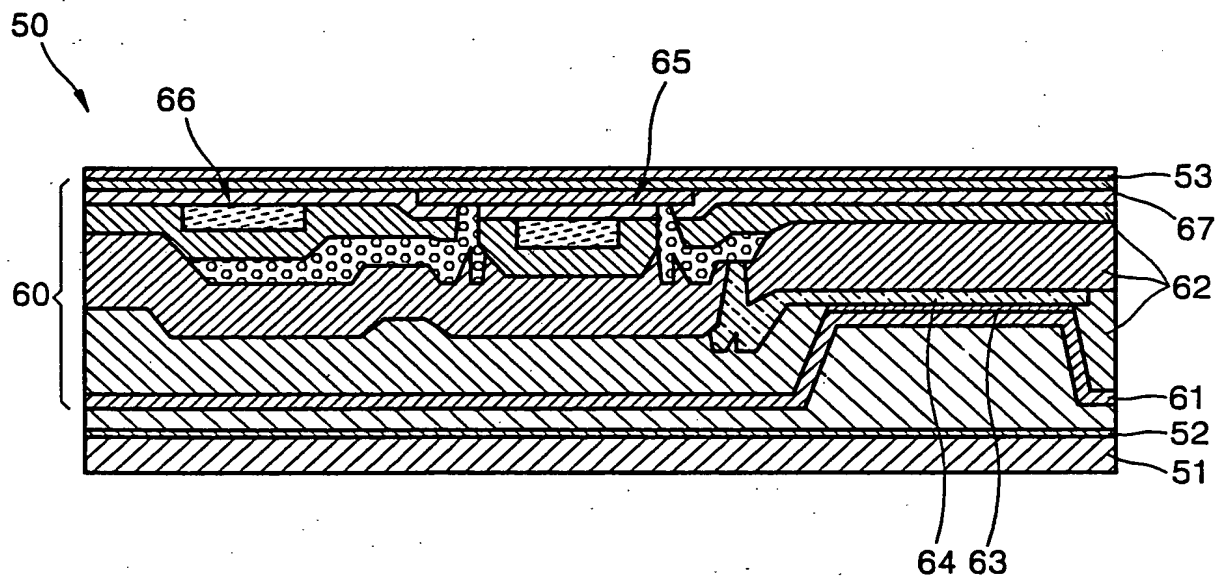


FIG. 9

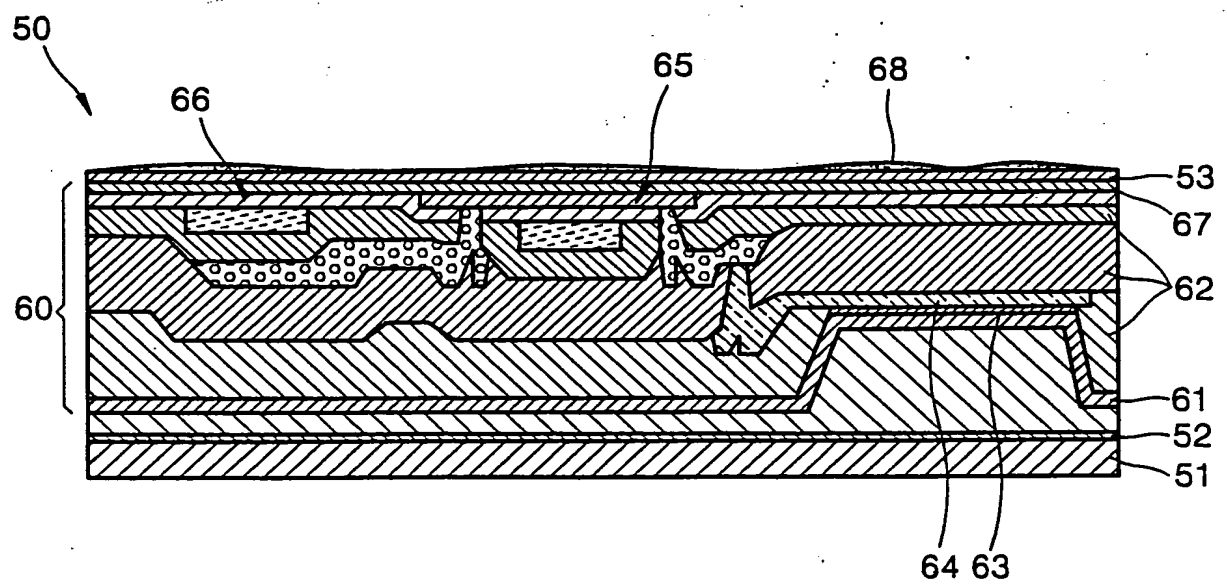


FIG. 10

